## PN Silicon Photodiode OP900SL



### Features:

- Narrow receiving angle
- Enhanced temperature range
- Ideal for direct mounting to PCBoard
- Fast switching speed
- Linear response vs.irradiance
- Mechanically and spectrally matched to OP123 emitters

#### **Description:**

Each **OP900SL** consists of a PN junction silicon photodiode mounted in a miniature glass-lensed hermetically sealed "pill" package. The lensing effect allows an acceptance half-angle of 18°, when measured from the optical axis to the half-power point.

The OP900SL is mechanically and spectrally matched to the OP123 series emitters.

<u>Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data,</u> and to Application Bulletin 202 for pill-type soldering to PCBoard.

### **Applications:**

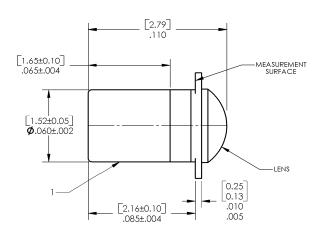
• Non-contact reflective object sensor

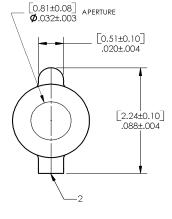
Ordering Information						
Part Number	Sensor	Viewing Angle				
OP900SL	Photodiode	35°				

Assembly line automation

1

- Machine automation
- Machine safety
- End of travel sensor
- Door sensor





DIMENSIONS ARE IN: [MILLIMETERS] INCHES

Pin
1
2



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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# **PN Silicon Photodiode**



### **Electrical Specifications**

Absolute Maximum Ratings (T <sub>A</sub> = 25° C unless otherwise noted)							
Reverse Voltage				100 V			
Operating Temperature Range				-65° C to +150° C			
Storage Temperature Range				-65° C to +125° C			
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 seconds with soldering iron]				260° C <sup>(1)</sup>			
Power Dissipation				50 mW <sup>(2)</sup>			
Electrical Characteristics (T <sub>A</sub> = 25° C unless otherwise noted)							
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SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS	
ΙL	Light Current	8	14	-	μA	$V_{R} = 10 V, E_{E} = 20 mW/cm^{2} {}^{(3)(4)}$	
ID	Dark Current	-	-	10	nA	$V_{R} = 10 V, E_{E} = 0^{(3)}$	
V <sub>(BR)R</sub>	Reverse Voltage Breakdown	100	150	-	V	I <sub>R</sub> = 100 μA	
t <sub>r</sub>	Rise Time	-	100	-	nc	$V_R$ = 50 V, I <sub>L</sub> = 8 $\mu$ A, R <sub>L</sub> = 1 k $\Omega$ (see test circuit)	
t <sub>f</sub>	Fall Time	-	100	-	ns		

Notes:

(1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.

(2) Derate linearly 0.5 mW/° C above 25° C.

(3) Junction temperature maintained at 25° C.

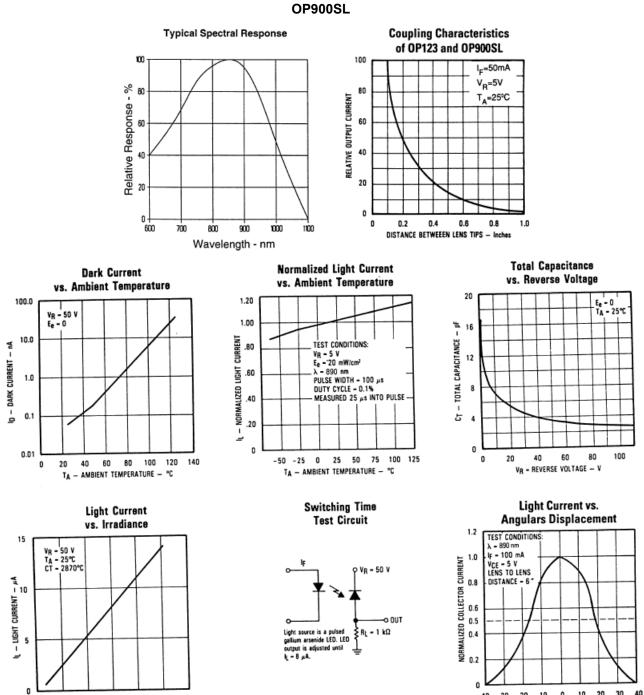
(4) Light source is an unfiltered tungsten bulb operating at CT = 2870 K or equivalent infrared source.

## **PN Silicon Photodiode**

OP900SL



### Performance



40 30 20 10 0 10 20 30 θ - ANGULAR DISPLACEMENT - Deg.

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16 20 24

8 12

Ee - IRRADIANCE - mW/cm<sup>2</sup>

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0 4